

# **Dual N-Channel Power MOSFET**

20V, 5.8A, 25mΩ

## **Features**

- Halogen-Free according to IEC 61249-2-21
- Suited for 1.8V drive applications
- Low profile package
- RoHS Compliant

#### **APPLICATION**

- Battery Pack
- Load Switch

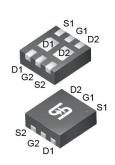
KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
$V_{DS}$		20	V	
	$V_{GS} = 4.5V$	25		
R <sub>DS(on)</sub> (max)	$V_{GS} = 2.5V$	35	mΩ	
	V <sub>GS</sub> = 1.8V	55		
$Q_g$		7.7	nC	

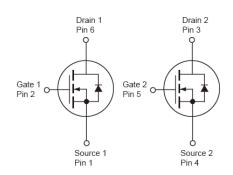












Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage		$V_{GS}$	±10	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		5.8	^
	$T_C = 100$ °C	I <sub>D</sub>	3.48	A
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	23.2	Α
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	0.62	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	TINU	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	200	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.

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ELECTRICAL SPECIFICAT	<b>FIONS</b> (T <sub>A</sub> = 25°C unles	s otherwise not	ed)			
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	0.4	0.6	0.8	V
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V	I <sub>DSS</sub>			1	μA
	$V_{GS} = 4.5V, I_D = 4A$			20	25	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3A$	R <sub>DS(on)</sub>		27	35	mΩ
	$V_{GS} = 1.8V, I_D = 2A$			39	55	
Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	g <sub>fs</sub>		6.5		S
Dynamic (Note 4)						
Total Gate Charge		$Q_g$		7.7	11	
Gate-Source Charge	$V_{DS} = 10V, I_D = 4A,$	$Q_{gs}$		0.9	1	nC
Gate-Drain Charge	$V_{GS} = 4.5V$	$Q_{gd}$		2.4	5	
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	C <sub>iss</sub>		535	775	
Output Capacitance		C <sub>oss</sub>		60	85	pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		34	50	
Switching (Note 5)						
Turn-On Delay Time		t <sub>d(on)</sub>		4.1	8	
Turn-On Rise Time	$V_{DD} = 10V, I_{D} = 1A,$	t <sub>r</sub>		11.6	22	
Turn-Off Delay Time	$V_{GS} = 4.5V, R_G = 25\Omega$	t <sub>d(off)</sub>		23.9	45	ns
Turn-Off Fall Time		t <sub>f</sub>		7.6	14	
Source-Drain Diode (Note 3)		•		•	•	
Continuous Source Current		I <sub>S</sub>			5.8	Α
ulsed Source Current		I <sub>SM</sub>			23.2	Α
Forward On Voltage	$V_{GS} = 0V, I_{S} = 1A$	V <sub>SD</sub>			1	V

#### Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

# **ORDERING INFORMATION**

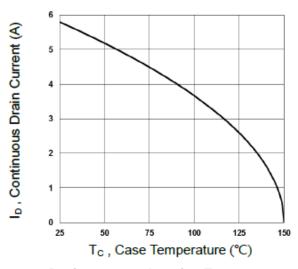
PART NO.	PACKAGE	PACKING		
TSM250N02DCQ RFG	TDFN 2x2	3,000pcs / 7" Reel		



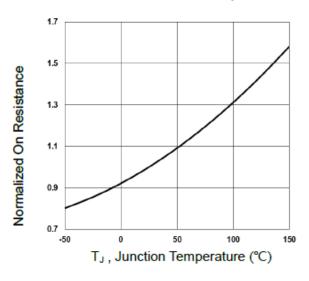
#### **CHARACTERISTICS CURVES**

(T<sub>C</sub> = 25°C unless otherwise noted)

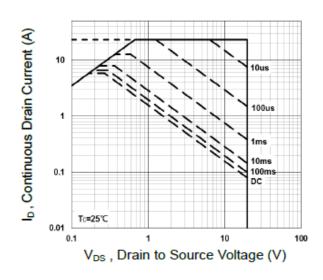
#### Continuous Drain Current vs. Tc



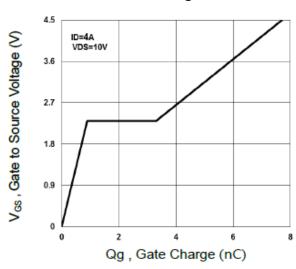
#### **On-Resistance vs. Junction Temperature**



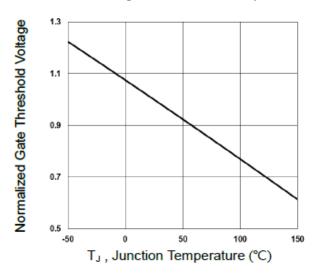
#### **Maximum Safe Operating Area**



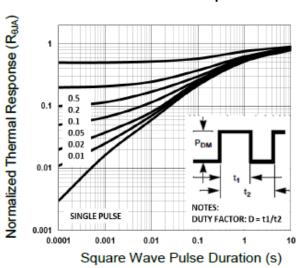
#### **Gate Charge**



Threshold Voltage vs. Junction Temperature



#### **Normalized Thermal Transient Impedance Curve**



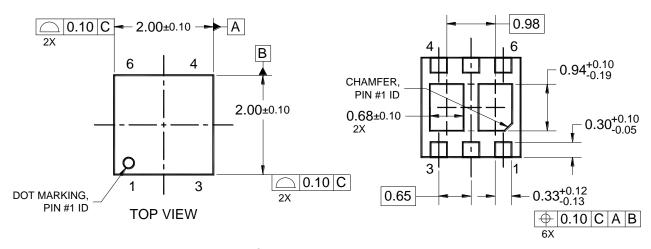
Version: C2212

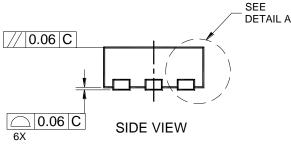
3

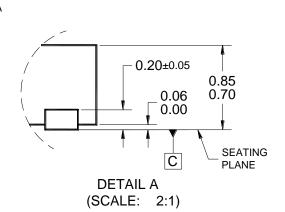


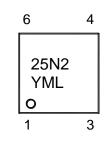
## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

#### TDFN2x2









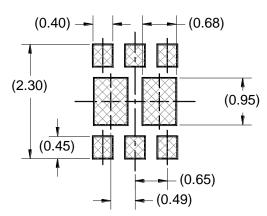
MARKING DIAGRAM (TOP VIEW)

P/N = DEVICE CODE

Y = YEAR CODE

M = MONTH CODE FOR HALOGEN FREE PRODUCT

L = LOT CODE (1~9, A~Z)



SUGGESTED PAD LAYOUT

NOTES: UNLESS OTHERWISE SPECIFIED

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- SEATING PLANE IS DEFINED BY TERMINAL BOTTOM SURFACE ONLY.
- 4. DWG NO. REF: HQ2SD07-TDFN2X2D-003 REV A



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